

Enhanced performance of Si-As-Se ovonic threshold switching selector

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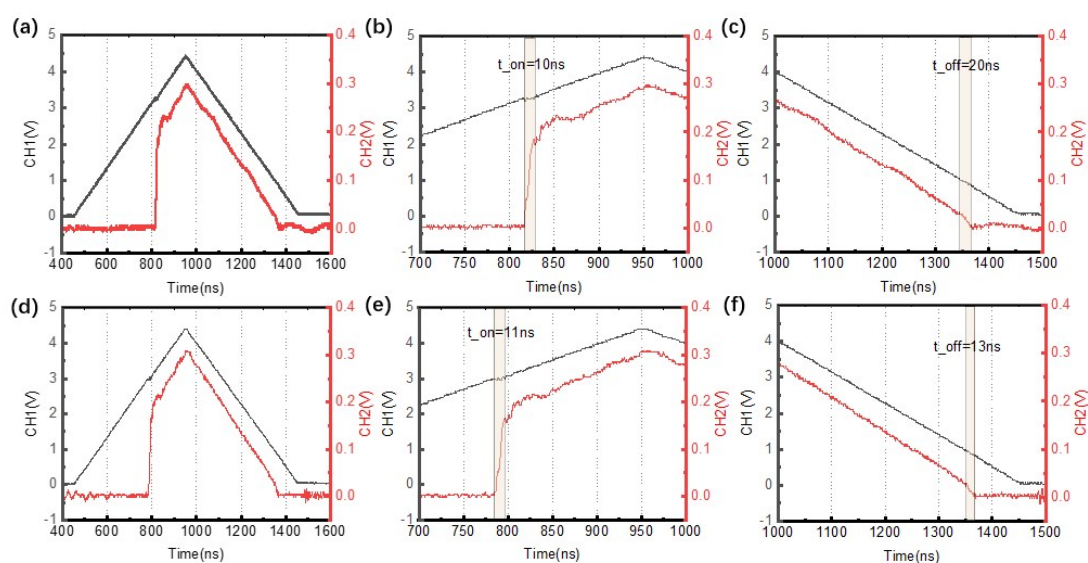


Fig.1. (a) and(d) Typical dynamical responses of the $\text{As}_{43}\text{Se}_{57}$ and $\text{Si}_9\text{As}_{39}\text{Se}_{52}$ based device under triangular voltage pulse respectively. (b) and(c) are the magnification version of ON and OFF switching edges for $\text{As}_{43}\text{Se}_{57}$. (e) and(f) are the magnification version of ON and OFF switching edges for $\text{Si}_9\text{As}_{39}\text{Se}_{52}$.